Low-power dual supply translating buffer Rev. 5 — 4 September 2013

Product data sheet

General description 1.

The 74AUP1T34 provides a single buffer with two separate supply voltages. Input A is designed to track $V_{CC(A)}$. Output Y is designed to track $V_{CC(Y)}$. Both, $V_{CC(A)}$ and $V_{CC(Y)}$ accepts any supply voltage from 1.1 V to 3.6 V. This feature allows universal low voltage interfacing between any of the 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V voltage nodes.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.1 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 1.1 V to 3.6 V. This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 1.1 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Wide supply voltage range:
 - V_{CC(A)}: 1.1 V to 3.6 V
 - V_{CC(Y)}: 1.1 V to 3.6 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Each port operates over the full 1.1 V to 3.6 V power supply range
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power dual supply translating buffer

3. Ordering information

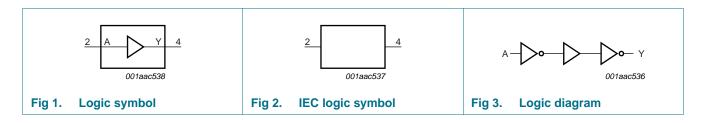
Table 1. Ordering	g information			
Type number	Package			
	Temperature range Name		Description	Version
74AUP1T34GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1T34GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
74AUP1T34GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
74AUP1T34GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP1T34GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202
74AUP1T34GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1T34GW	pQ
74AUP1T34GM	pQ
74AUP1T34GF	pQ
74AUP1T34GN	pQ
74AUP1T34GS	pQ
74AUP1T34GX	pQ

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

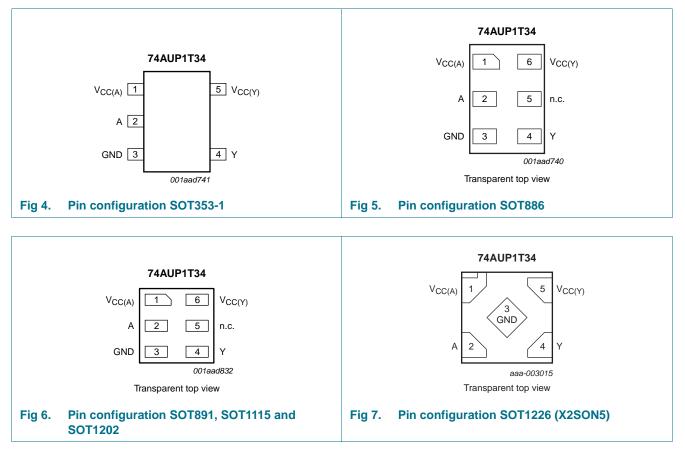
5. Functional diagram



Low-power dual supply translating buffer

Pinning information 6.

6.1 Pinning



6.2 Pin description

Symbol	Pin		Description		
	TSSOP5 and X2SON5	XSON6			
V _{CC(A)}	1	1	supply voltage port A		
A	2	2	data input A		
GND	3	3	ground (0 V)		
Y	4	4	data output Y		
n.c.	-	5	not connected		
V _{CC(Y)}	5 6		supply voltage port Y		

74AUP1T34 **Product data sheet**

Low-power dual supply translating buffer

7. Functional description

Table 4. Fu	unction table ^[1]	
Input		Output
Α		Y
L		L
Н		Н

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+4.6	V
V _{CC(Y)}	supply voltage Y		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_{O} = 0 V \text{ to } V_{CC(Y)}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

For XSON6 and X2SON5 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

Low-power dual supply translating buffer

9. Recommended operating conditions

Table 6.	Recommended operating cond	itions			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		1.1	3.6	V
V _{CC(Y)}	supply voltage Y		1.1	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage		0	V _{CC(Y)}	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	control and data inputs; $V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level	$V_{CC(A)}$ = 1.1 V to 1.95 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	$0.65 \times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level	$V_{I} = V_{IH}$				
	output voltage	$I_{O} = -20 \ \mu\text{A}; \ V_{CC(A)} = V_{CC(Y)} = 1.1 \ V \text{ to } 3.6 \ V$	$V_{CC(Y)} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.75 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level	$V_{I} = V_{IL}$				
	output voltage	$I_{O} = 20 \ \mu\text{A}; \ V_{CC(A)} = V_{CC(Y)} = 1.1 \ V \text{ to } 3.6 \ V$	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC(Y)}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O} = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_{I} = 0 V \text{ to } 3.6 V; V_{CC(A)} = V_{CC(Y)} = 1.1 V \text{ to } 3.6 V$	-	-	±0.1	μA
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Low-power dual supply translating buffer

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{OFF}	power-off leakage current	A input; $V_1 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$; $V_{CC(Y)} = 0 V$ to 3.6 V	-	-	±0.2	μA
		Y output; $V_0 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; $V_I = 0 V$ or 3.6 V; $V_{CC(Y)} = 0 V$	-	-	±0.2	μA
∆l _{OFF}	additional power-off	A input; $V_I = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 0.2 V; $V_{CC(Y)} = 0 V$ to 3.6 V	-	-	±0.2	μA
	leakage current	Y output; $V_0 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; V _I = 0 V or 3.6 V; $V_{CC(Y)} = 0 V$ to 0.2 V	-	-	±0.2	μA
СС	supply current	port A; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.5	μΑ
	<pre>ieakage current additional power-off leakage current supply current supply current input capacitance output capacitance b = -40 °C to +85 °C HIGH-level input voltage LOW-level input voltage</pre>	$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	-	0.5	μΑ
		port A and port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	0.5	μA
∆l _{CC}		A input; $V_{CC(A)} = 3.3$ V; $V_{CC(Y)} = 0$ V to 3.6 V; $V_I = V_{CC(A)} - 0.6$ V	-	-	40	μA
Cı		A input; $V_{CC(A)} = V_{CC(Y)} = 0$ V to 3.6 V; V _I = GND or V _{CC(A)}	-	1.0	-	pF
Co	-	Y output; $V_O = GND$; $V_{CC(Y)} = 0$ V; $V_{CC(A)} = 0$ V to 3.6 V	-	1.8	-	pF
T _{amb} = –	40 °C to +85 °C					
$ \begin{split} & \label{eq:rescaled_rescale} \begin{tabular}{ c c c c c } lice constraints of the set of the $						
	input voltage	$V_{CC(A)}$ = 2.3 V to 2.7 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	1.6	-	-	V
		$V_{CC(A)}$ = 3.0 V to 3.6 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	2.0	-	-	V
V _{IL}		$V_{CC(A)}$ = 1.1 V to 1.95 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)}$ = 2.3 V to 2.7 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.7	V
		$V_{CC(A)}$ = 3.0 V to 3.6 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.9	V
V _{он}		$V_{I} = V_{IH}$				
	output voltage	I_O = –20 $\mu\text{A};$ $V_{CC(\text{A})}$ = $V_{CC(\text{Y})}$ = 1.1 V to 3.6 V	$V_{CC(Y)}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.7\times V_{\text{CC}(\text{Y})}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.55	-	-	V

Low-power dual supply translating buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level	$V_{I} = V_{IL}$				
	output voltage	$I_O = 20 \ \mu\text{A}$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \ V$ to 3.6 V	-	-	0.1	V
		I_{O} = 1.1 mA; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V	-	-	$0.3 \times V_{CC(Y)}$	V
	output voltage input leakage current power-off leakage current power-off leakage current supply current	$I_O = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.37	V
		I_{O} = 1.9 mA; $V_{CC(A)} = V_{CC(Y)}$ = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.45	V
lı		$V_I = 0 V$ to 3.6 V; $V_{CC(A)} = V_{CC(Y)} = 1.1 V$ to 3.6 V	-	-	±0.5	μA
I _{OFF}		A input; $V_I = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$; $V_{CC(Y)} = 0 V$ to 3.6 V	-	-	±0.5	μA
		Y output; $V_0 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; V _I = 0 V or 3.6 V; $V_{CC(Y)} = 0 V$	-	-	±0.5	μA
ΔI_{OFF}		A input; $V_I = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 0.2 V; $V_{CC(Y)} = 0 V$ to 3.6 V	-	-	±0.6	μA
	leakage current	Y output; $V_0 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; V _I = 0 V or 3.6 V; $V_{CC(Y)} = 0 V$ to 0.2 V	-	-	±0.6	μA
I _{CC}	supply current	port A; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.9	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	0.0	-	μA
		port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
	power-off leakage current	$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	-	0.9	μA
		port A and port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	0.9	μA
Δl _{CC}		A input; $V_{CC(A)} = 3.3 \text{ V}$; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_I = V_{CC(A)} - 0.6 \text{ V}$	-	-	50	μA
T _{amb} = –	40 °C to +125 °C					
V _{IH}	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.7\times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		V _{CC(A)} = 3.0 V to 3.6 V; V _{CC(Y)} = 1.1 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.3 imes V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)}$ = 3.0 V to 3.6 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.9	V

Table 7. Static characteristics ...continued

Low-power dual supply translating buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{он}	HIGH-level	$V_I = V_{IH}$				
	output voltage	$I_O = -20 \ \mu\text{A}$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \ \text{V}$ to 3.6 V	$V_{CC(Y)} - 0.11$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.6 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	0.93	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level	$V_{I} = V_{IL}$				
	output voltage	$I_{O} = 20 \ \mu A; V_{CC(A)} = V_{CC(Y)} = 1.1 \ V \text{ to } 3.6 \ V$	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC(Y)}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_{I} = 0 V \text{ to } 3.6 V; V_{CC(A)} = V_{CC(Y)} = 1.1 V \text{ to } 3.6 V$	-	-	±0.75	μA
OFF	power-off leakage current	A input; $V_I = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$; $V_{CC(Y)} = 0 V$ to 3.6 V	-	-	±0.75	μΑ
		Y output; $V_0 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; V _I = 0 V or 3.6 V; $V_{CC(Y)} = 0 V$	-	-	±0.75	μΑ
∆I _{OFF}	additional power-off	A input; $V_I = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 0.2 V; $V_{CC(Y)} = 0 V$ to 3.6 V	-	-	±0.75	μA
	leakage current	Y output; $V_0 = 0 V$ to 3.6 V; $V_{CC(A)} = 0 V$ to 3.6 V; V _I = 0 V or 3.6 V; $V_{CC(Y)} = 0 V$ to 0.2 V	-	-	±0.75	μA
СС	supply current	port A; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	1.4	μA
		$V_{CC(A)} = 0 V; V_{CC(Y)} = 3.6 V$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μA
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	1.4	μA
		port A and port Y; $V_1 = GND$ or $V_{CC(A)}$; $I_0 = 0$ A; $V_{CC(A)} = V_{CC(Y)} = 1.1$ V to 3.6 V	-	-	1.4	μA
۵l _{CC}	additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_I = V_{CC(A)} - 0.6 \text{ V}$	-	-	75	μΑ

Static characteristics ... continued Table 7.

8 of 24

Low-power dual supply translating buffer

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

	Parameter	Conditions		25 °C			-4	Unit		
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F; V _{CC(A)} = 1.1 V to	1.3 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 V \text{ to } 1.3 V$		2.6	9.8	25.4	2.3	25.9	25.9	ns
		$V_{CC(Y)} = 1.4 V$ to 1.6 V		2.4	7.1	15.3	2.2	16.3	16.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	6.0	12.7	1.9	13.8	14.3	ns
		$V_{CC(Y)}$ = 2.3 V to 2.7 V		2.0	5.1	9.8	2.0	10.5	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.7	8.8	1.9	9.1	9.3	ns
Հ _L = 5 pl	F; V _{CC(A)} = 1.4 V to	1.6 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.1	23.9	2.0	24.5	24.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	6.4	13.6	1.9	14.7	15.2	ns
	V _{CC(Y)} = 1.65 V to 1.95 V		1.8	5.3	10.9	1.6	12.1	12.6	ns	
	$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	4.3	7.8	1.6	8.7	9.2	ns	
		V _{CC(Y)} = 3.0 V to 3.6 V		1.8	3.9	6.6	1.6	7.1	7.5	ns
C _L = 5 pl	F; V _{CC(A)} = 1.65 V to	1.95 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.2	8.8	23.2	1.9	23.9	24.0	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		2.0	6.0	13.0	1.8	14.1	14.6	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		1.8	4.9	10.3	1.5	11.4	12.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	3.9	7.2	1.5	8.0	8.5	ns
		V _{CC(Y)} = 3.0 V to 3.6 V		1.7	3.5	5.9	1.5	6.4	6.8	ns
C _L = 5 pl	F; V _{CC(A)} = 2.3 V to 2	2.7 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.2	8.4	22.8	1.9	23.4	23.4	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		1.9	5.7	12.3	1.8	13.4	14.0	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		1.7	4.6	9.6	1.5	10.7	11.2	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.5	6.3	1.5	7.2	7.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.1	5.1	1.4	5.6	6.0	ns
C _L = 5 pl	F; V _{CC(A)} = 3.0 V to 3	3.6 V								
pd		A to Y; see Figure 8	[2]							
	-	V _{CC(Y)} = 1.1 V to 1.3 V		2.2	8.1	22.5	1.9	22.9	22.9	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.4	12.0	1.8	12.9	13.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	4.3	9.2	1.5	10.2	10.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.3	6.0	1.5	6.7	7.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	2.9	4.8	1.4	5.2	5.5	ns

9 of 24

Low-power dual supply translating buffer

Symbol	Parameter	Conditions			25 °C		-4	0 °C to +′	125 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 10 p	oF; V _{CC(A)} = 1.1 V to	1.3 V								
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	10.7	27.1	2.5	27.6	27.6	ns
		$V_{CC(Y)} = 1.4 V \text{ to } 1.6 V$		2.6	7.7	16.7	2.3	17.5	17.6	ns
		$V_{CC(Y)}$ = 1.65 V to 1.95 V		2.7	6.6	13.4	2.4	14.2	14.7	ns
		$V_{CC(Y)}$ = 2.3 V to 2.7 V		2.2	5.6	10.3	2.2	11.0	11.4	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	5.3	9.5	2.2	9.7	10.0	ns
C _L = 10 p	oF; V _{CC(A)} = 1.4 V to	1.6 V								
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.4	10.0	25.6	2.2	26.1	26.1	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	7.0	15.0	2.0	15.8	16.4	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		2.4	5.9	11.6	2.1	12.5	13.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	4.8	8.4	1.9	9.2	9.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	4.4	7.4	1.9	7.7	8.1	ns
C _L = 10 p	oF; V _{CC(A)} = 1.65 V t	o 1.95 V								
t _{pd}	propagation delay	A to Y; see Figure 8								
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.7	24.8	2.1	25.5	25.7	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		2.3	6.6	14.3	2.0	15.3	15.8	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		2.3	5.5	11.0	2.0	11.9	12.5	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.9	4.4	7.7	1.8	8.6	9.0	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.0	6.6	1.8	7.1	7.4	ns
C _L = 10 p	oF; V _{CC(A)} = 2.3 V to	2.7 V								
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.3	24.4	2.1	25.1	25.1	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		2.2	6.3	13.6	1.9	14.6	15.1	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		2.2	5.1	10.3	2.0	11.2	11.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	4.1	6.9	1.8	7.7	8.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.6	5.8	1.7	6.3	6.6	ns
C _L = 10 p	oF; V _{CC(A)} = 3.0 V to	9 3.6 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.3	9.0	24.2	2.1	24.6	24.6	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		2.2	6.0	13.3	1.9	14.1	14.6	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		2.2	4.9	9.9	2.0	10.6	11.2	ns
		V _{CC(Y)} = 2.3 V to 2.7 V		1.8	3.9	6.5	1.8	7.3	7.7	ns
		V _{CC(Y)} = 3.0 V to 3.6 V		2.0	3.5	5.4	1.7	5.8	6.2	ns

Table 8. Dynamic characteristics ... continued

Low-power dual supply translating buffer

Symbol Parameter		Conditions		25 °C			–40 °C to +125 °C			Unit
				Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 15	$F; V_{CC(A)} = 1.1 V to$	1.3 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.0	11.5	28.6	2.8	29.2	29.2	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.1	8.3	17.3	2.7	18.6	19.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.8	7.1	14.1	2.7	15.2	15.8	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	6.1	11.1	2.7	11.6	12.1	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.9	5.7	9.9	2.6	10.3	10.6	ns
C _L = 15	oF; V _{CC(A)} = 1.4 V to	9 1.6 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.8	10.8	27.1	2.6	27.7	27.7	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.8	7.6	15.7	2.4	17.0	17.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.5	6.3	12.3	2.4	13.5	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.3	5.3	9.2	2.4	9.9	10.3	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.6	4.9	7.8	2.3	8.3	8.7	ns
C _L = 15 J	oF; V _{CC(A)} = 1.65 V t	to 1.95 V								
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.7	10.5	26.4	2.5	27.1	27.3	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.7	7.2	15.0	2.3	16.4	17.0	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	6.0	11.7	2.3	12.8	13.5	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.2	4.9	8.5	2.2	9.2	9.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	4.5	7.1	2.2	7.7	8.0	ns
C _L = 15	oF; V _{CC(A)} = 2.3 V to	2.7 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	10.1	26.0	2.4	26.7	26.7	ns
		$V_{CC(Y)} = 1.4 V \text{ to } 1.6 V$		2.7	6.9	14.3	2.3	15.7	16.3	ns
		$V_{CC(Y)}$ = 1.65 V to 1.95 V		2.4	5.6	10.9	2.2	12.1	12.7	ns
		$V_{CC(Y)}$ = 2.3 V to 2.7 V		2.1	4.5	7.6	2.2	8.4	8.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	4.1	6.2	2.1	6.8	7.2	ns
C _L = 15	oF; V _{CC(A)} = 3.0 V to	9 3.6 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	9.8	25.7	2.4	26.2	26.2	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.7	6.6	14.0	2.3	15.2	15.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	5.4	10.5	2.2	11.6	12.1	ns
		$V_{CC(Y)}$ = 2.3 V to 2.7 V		2.1	4.3	7.3	2.2	7.9	8.4	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	3.9	5.9	2.1	6.4	6.8	ns

Table 8. Dynamic characteristics ... continued

Low-power dual supply translating buffer

Symbol	Parameter	Conditions			25 °C			–40 °C to +125 °C		
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 30	oF; V _{CC(A)} = 1.1 V to	1.3 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.7	13.7	32.9	3.5	33.5	33.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.6	9.8	19.5	3.6	20.9	21.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.7	8.4	15.9	3.5	17.0	17.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		3.0	7.2	12.2	3.4	12.7	13.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.8	6.8	10.9	3.4	12.2	12.5	ns
C _L = 30	oF; V _{CC(A)} = 1.4 V to	1.6 V								
pd	d propagation delay A to Y; see Figure 8		[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.5	13.1	31.5	3.2	32.0	32.0	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.3	9.1	17.8	3.3	19.2	19.9	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		3.4	7.6	14.2	3.2	15.4	16.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.8	6.4	10.3	3.1	11.0	11.5	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.5	5.9	8.9	3.1	10.1	10.5	ns
C _L = 30	oF; V _{CC(A)} = 1.65 V t	o 1.95 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.4	12.7	30.7	3.1	31.5	31.5	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		3.2	8.8	17.2	3.2	18.7	19.3	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		3.3	7.3	13.5	3.1	14.7	15.4	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	6.0	9.6	3.0	10.4	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.4	5.6	8.2	2.9	9.4	9.8	ns
C _L = 30	oF; V _{CC(A)} = 2.3 V to	2.7 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		3.3	12.4	30.3	3.1	31.0	31.0	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		3.2	8.4	16.5	3.1	18.0	18.7	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		3.2	6.9	12.8	3.0	14.0	14.6	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.6	8.8	2.9	9.6	10.1	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.3	5.2	7.3	2.9	8.5	9.0	ns
C = 30	oF; V _{CC(A)} = 3.0 V to	3.6 V								
pd	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	12.0	30.0	3.1	30.5	30.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.2	8.1	16.2	3.1	17.5	18.1	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		3.2	6.7	12.4	3.0	13.4	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.5	8.5	2.9	9.1	9.6	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.2	5.0	7.0	2.9	8.1	8.5	ns

Table 8. Dynamic characteristics ... continued

Low-power dual supply translating buffer

Symbol	Parameter	Conditions	25 °C			-40	0 °C to +′	125 °C	Unit	
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF			1					
	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}(A)}$	[3][4]							
		$V_{CC(A)} = V_{CC(Y)} = 1.2 V$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.5 V$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.8 V$		-	4.1	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 2.5 V$		-	4.2	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 3.3 V$		-	4.6	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_1 = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms

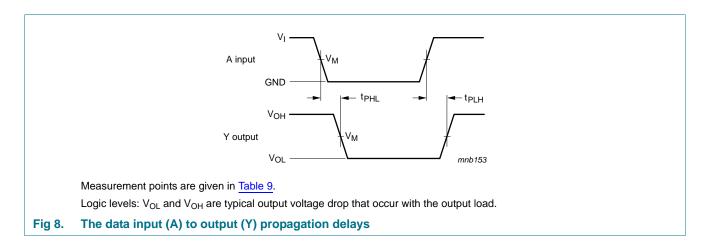


Table 9. **Measurement points**

Supply voltage	Output	Input			
V _{CC(A)} /V _{CC(Y)}	V _M	V _M	VI	$t_r = t_f$	
1.1 V to 3.6 V	$0.5 imes V_{CC(Y)}$	$0.5 imes V_{CC(A)}$	V _{CC(A)}	≤ 3.0 ns	

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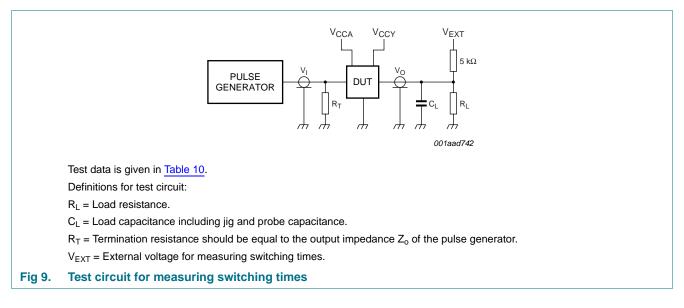


Table 10. Test data

Supply voltage	Load		V _{EXT}
V _{CC(A)} /V _{CC(Y)}	CL	R _L ^[1]	t _{PLH} , t _{PHL}
1.1 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

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13. Package outline

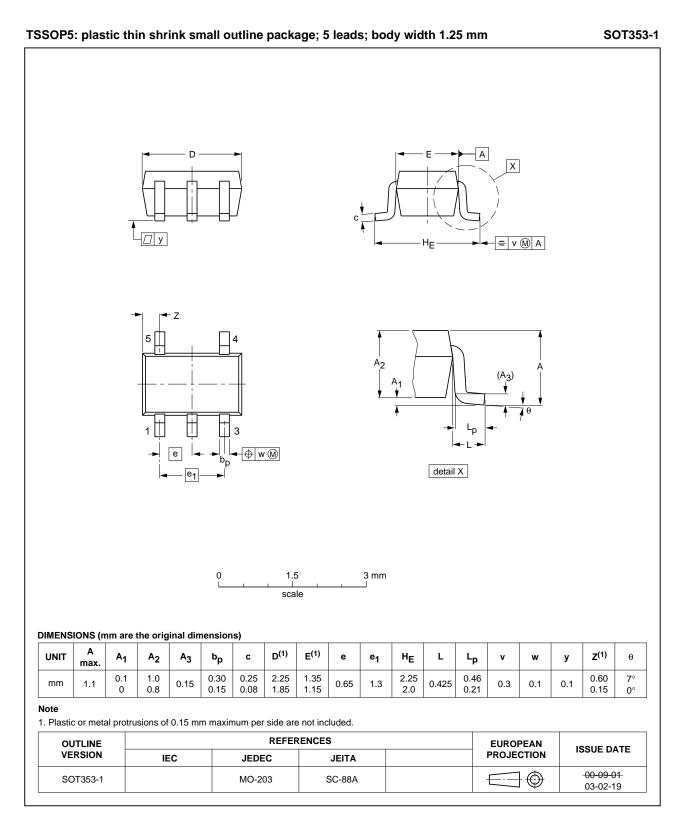


Fig 10. Package outline SOT353-1 (TSSOP5)

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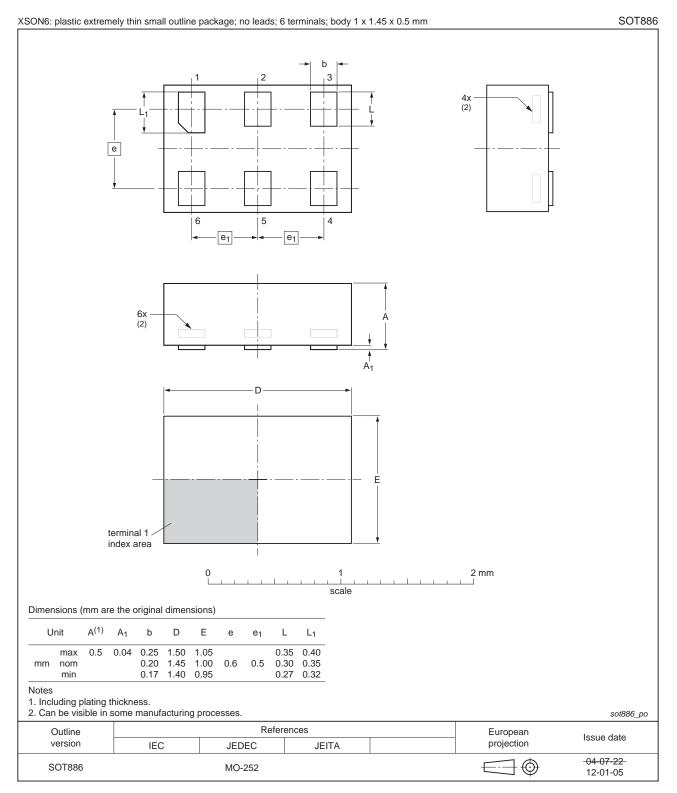
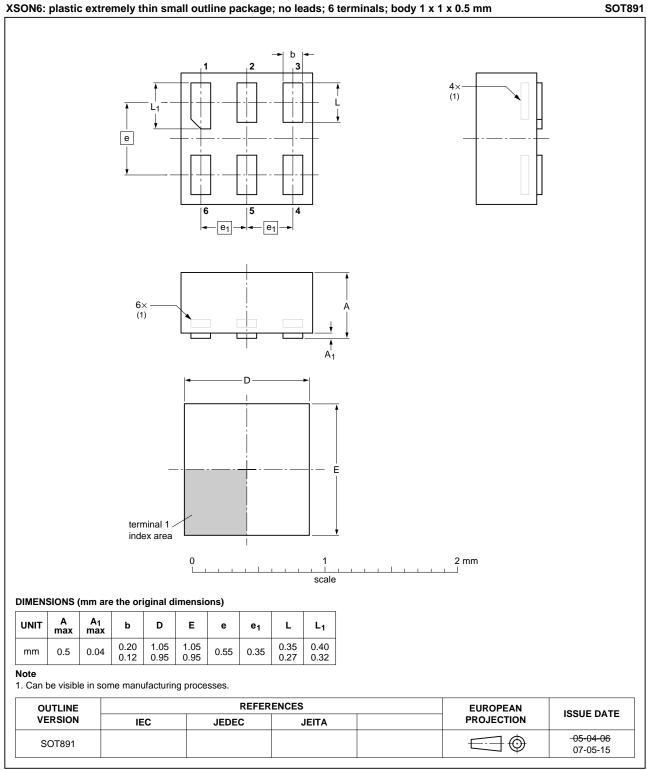


Fig 11. Package outline SOT886 (XSON6)

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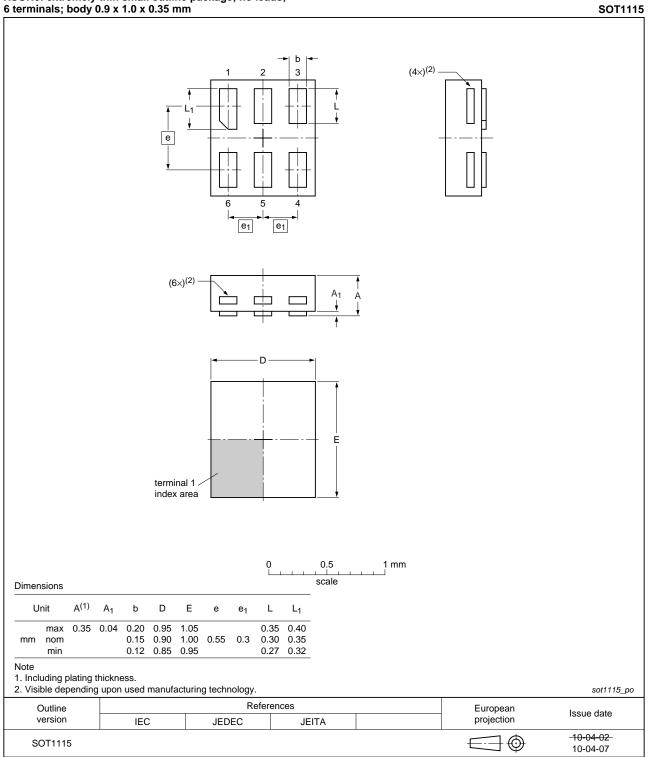


XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

Fig 12. Package outline SOT891 (XSON6)

74AUP1T34 **Product data sheet**

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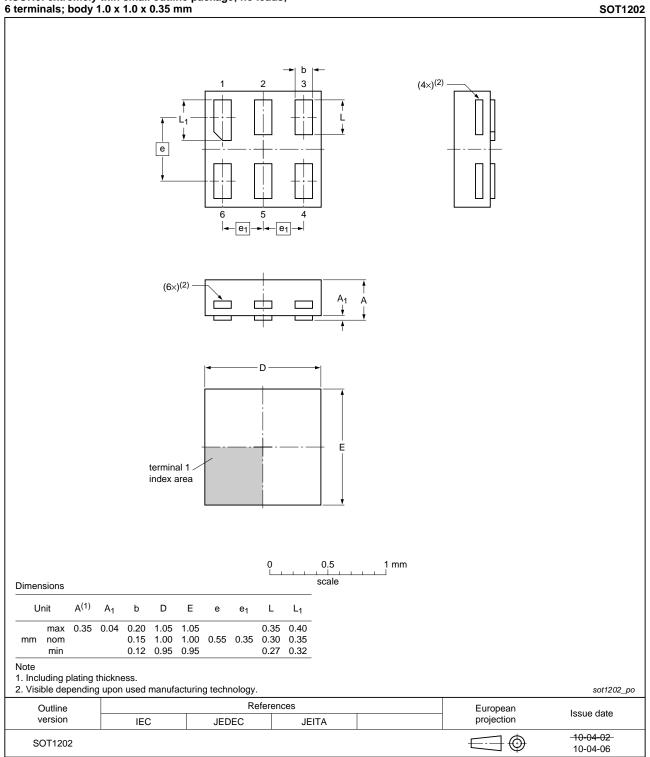


XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1115 (XSON6)

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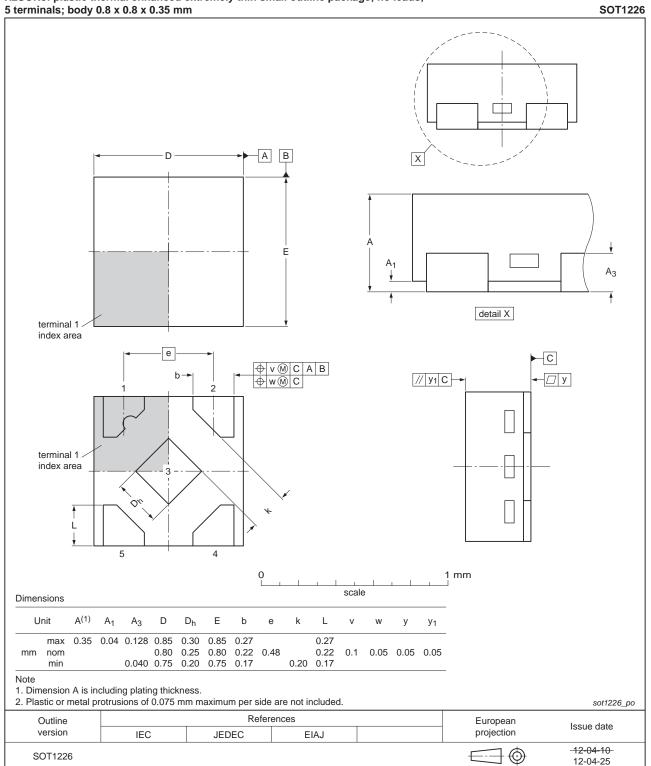


XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1202 (XSON6)

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X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;

Fig 15. Package outline SOT1226 (X2SON5)

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14. Abbreviations

AcronymDescriptionCDMCharged Device ModelDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model		Table 11. Abbreviations	
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model		Acronym Description	
ESD ElectroStatic Discharge HBM Human Body Model	lodel	CDM Charged Device	
HBM Human Body Model	t	DUT Device Under Te	
	harge	ESD ElectroStatic Dis	
	el	HBM Human Body Mo	
MM Machine Model		MM Machine Model	

15. Revision history

Table 12.Revision history

	· · · · · · · · · · · · · · · · · · ·			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T34 v.5	20130904	Product data sheet	-	74AUP1T34 v.4
Modifications:	 Added type 	e number 74AUP1T34GX (S	OT1226)	
74AUP1T34 v.4	20120316	Product data sheet	-	74AUP1T34 v.3
Modifications:	 Package o 	utline drawing of SOT886 (F	igure 11) modified.	
74AUP1T34 v.3	20111128	Product data sheet	-	74AUP1T34 v.2
Modifications:	 Legal page 	es updated.		
74AUP1T34 v.2	20100819	Product data sheet	-	74AUP1T34 v.1
74AUP1T34 v.1	20061204	Product data sheet	-	-

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16. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning 3
6.2	Pin description 3
7	Functional description 4
8	Limiting values 4
9	Recommended operating conditions 5
10	Static characteristics
11	Dynamic characteristics 9
12	Waveforms
13	Package outline 15
14	Abbreviations
15	Revision history 21
16	Legal information 22
16.1	Data sheet status
16.2	Definitions 22
16.3	Disclaimers 22
16.4	Trademarks 23
17	Contact information 23
18	Contents 24

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